

# LC<sup>2</sup>MOS 4-/8-Channel High Performance Analog Multiplexers

# ADG408/ADG409

#### **FEATURES**

44 V Supply Maximum Ratings  $V_{SS}$  to  $V_{DD}$  Analog Signal Range Low On Resistance (100  $\Omega$  max) Low Power ( $I_{SUPPLY}$  < 75  $\mu$ A) Fast Switching Break-Before-Make Switching Action Plug-in Replacement for DG408/DG409

#### **APPLICATIONS**

Audio and Video Routing Automatic Test Equipment Data Acquisition Systems Battery Powered Systems Sample and Hold Systems Communication Systems

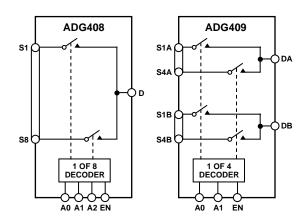
#### **GENERAL DESCRIPTION**

The ADG408 and ADG409 are monolithic CMOS analog multiplexers comprising eight single channels and four differential channels respectively. The ADG408 switches one of eight inputs to a common output as determined by the 3-bit binary address lines A0, A1 and A2. The ADG409 switches one of four differential inputs to a common differential output as determined by the 2-bit binary address lines A0 and A1. An EN input on both devices is used to enable or disable the device. When disabled, all channels are switched OFF.

The ADG408/ADG409 are designed on an enhanced LC<sup>2</sup>MOS process which provides low power dissipation yet gives high switching speed and low on resistance. Each channel conducts equally well in both directions when ON and has an input signal range that extends to the supplies. In the OFF condition, signal levels up to the supplies are blocked. All channels exhibit breakbefore-make switching action, preventing momentary shorting when switching channels. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

The ADG408/ADG409 are improved replacements for the DG408/DG409 Analog Multiplexers.

## FUNCTIONAL BLOCK DIAGRAMS



## PRODUCT HIGHLIGHTS

- Extended Signal Range
   The ADG408/ADG409 are fabricated on an enhanced LC<sup>2</sup>MOS process giving an increased signal range that extends to the supply rails.
- 2. Low Power Dissipation
- 3 Low Ron
- 4. Single Supply Operation
  For applications where the analog signal is unipolar, the ADG408/ADG409 can be operated from a single rail power supply. The parts are fully specified with a single +12 V power supply and will remain functional with single supplies as low as +5 V.

# ADG408/ADG409—SPECIFICATIONS

**DUAL SUPPLY**<sup>1</sup>  $(V_{DD} = +15 \text{ V}, V_{SS} = -15 \text{ V}, \text{GND} = 0 \text{ V}, \text{ unless otherwise noted})$ 

	B Version		T Version			
Parameter	+25°C	-40°C to +85°C	+25°C	-55°C to +125°C	Units	Test Conditions/Comments
ANALOG SWITCH						
Analog Signal Range		$V_{SS}$ to $V_{DD}$		$V_{SS}$ to $V_{DD}$	V	
$R_{ m ON}$	40	33 · · · DD	40	33 · DD	Ω typ	$V_D = \pm 10 \text{ V}, I_S = -10 \text{ mA}$
	100	125	100	125	$\Omega$ max	
$\Delta R_{ m ON}$	15		15		Ω max	$V_D = +10 \text{ V}, -10 \text{ V}$
LEAKAGE CURRENTS						
Source OFF Leakage I <sub>S</sub> (OFF)	±0.5	±50	±0.5	±50	nA max	$V_D = \pm 10 \text{ V}, V_S = \mp 10 \text{ V};$
D : OFFI 1 1 (OFF)						Test Circuit 2
Drain OFF Leakage I <sub>D</sub> (OFF) ADG408	±1	±100	±1	±100	n A marr	$V_D = \pm 10 \text{ V}; V_S = \mp 10 \text{ V};$ Test Circuit 3
ADG408 ADG409	±1	±100 ±50	$\begin{array}{cccc} & \pm 1 \\ & \pm 1 \end{array}$	±100 ±50	nA max nA max	Test Circuit 5
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)	<u>-1</u>	± 90	1	± 90	III I III ax	$V_{S} = V_{D} = \pm 10 \text{ V};$
ADG408	±1	$\pm 100$	±1	±100	nA max	Test Circuit 4
ADG409	±1	±50	±1	±50	nA max	
DIGITAL INPUTS						
Input High Voltage, V <sub>INH</sub>		2.4		2.4	V min	
Input Low Voltage, V <sub>INL</sub>		0.8		0.8	V max	
Input Current						
I <sub>INL</sub> or I <sub>INH</sub>		±10		±10	μA max	$V_{IN} = 0 \text{ or } V_{DD}$
C <sub>IN</sub> , Digital Input Capacitance	8		8		pF typ	f = 1 MHz
DYNAMIC CHARACTERISTICS <sup>2</sup>						
t <sub>TRANSITION</sub>		120		120	ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
		250		250	ns max	$V_{S1} = \pm 10 \text{ V}, V_{SS} = \mp 10 \text{ V};$ Test Circuit 5
$t_{OPEN}$	10	10	10	10	ns min	$R_L = 300 \Omega$ , $C_L = 35 pF$ ;
COPEN	10	10		10	113 111111	$V_S = +5 \text{ V}$ ; Test Circuit 6
$t_{ON}$ (EN)	85	125	85	125	ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
	150	225	150	225	ns max	$V_S = +5 \text{ V}$ ; Test Circuit 7
$t_{OFF}$ (EN)		65		65	ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
Change Injection	20	150	20	150	ns max	$V_S = +5 \text{ V}$ ; Test Circuit 7
Charge Injection	20		20		pC typ	$V_S = 0 V$ , $R_S = 0 \Omega$ , $C_L = 10 nF$ ; Test Circuit 8
OFF Isolation	<b>-75</b>		<b>-75</b>		dB typ	$R_L = 1 \text{ k}\Omega, f = 100 \text{ kHz};$
011 1001111011			.,		uz typ	$V_{EN} = 0 \text{ V}$ ; Test Circuit 9
Channel-to-Channel Crosstalk	85		85		dB typ	$R_L = 1 \text{ k}\Omega, f = 100 \text{ kHz};$
					_	Test Circuit 10
$C_{S}$ (OFF)	11		11		pF typ	f = 1  MHz
C <sub>D</sub> (OFF) ADG408	40		40		pF typ	f = 1 MHz
ADG400 ADG409	20		20		pF typ	
$C_D$ , $C_S$ (ON)					P- GP	f = 1  MHz
ADG408	54		54		pF typ	
ADG409	34		34		pF typ	
POWER REQUIREMENTS						
$I_{ m DD}$		1		1	μA typ	$V_{\rm IN} = 0 \text{ V}, V_{\rm EN} = 0 \text{ V}$
		5		5	μA max	
$I_{SS}$		1		1	μA typ	
Ī	100	5	100	5	μA max	$V_{-} = 0 V V - 2 4 V$
$ m I_{DD}$	200	500	200	500	μA typ μA max	$V_{IN} = 0 \text{ V}, V_{EN} = 2.4 \text{ V}$
	200	J00 	200	J00 	μαπιιαχ	

Specifications subject to change without notice.

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NOTES

<sup>1</sup>Temperature ranges are as follows: B Version: -40°C to +85°C; T Version: -55°C to +125°C.

<sup>&</sup>lt;sup>2</sup>Guaranteed by design, not subject to production test.

# **SINGLE SUPPLY**<sup>1</sup> ( $V_{DD} = +12 \text{ V}, V_{SS} = 0 \text{ V}, \text{GND} = 0 \text{ V}, \text{ unless otherwise noted}$ )

	B V	ersion	TV	ersion		
Parameter	+25°C	-40°C to +85°C	+25°C	-55°C to +125°C	Units	Test Conditions/Comments
ANALOG SWITCH						
Analog Signal Range		0 to $V_{\mathrm{DD}}$	0.0	$0$ to $V_{\mathrm{DD}}$	V	
R <sub>ON</sub>	90		90		Ω typ	$V_D = +3 \text{ V}, +10 \text{ V}, I_S = -1 \text{ mA}$
LEAKAGE CURRENTS		. = 0				
Source OFF Leakage $I_S$ (OFF)  Drain OFF Leakage $I_D$ (OFF)	±0.5	±50	±0.5	±50	nA max	$V_D = 8 \text{ V/0 V}, V_S = 0 \text{ V/8 V};$ Test Circuit 2 $V_D = 8 \text{ V/0 V}, V_S = 0 \text{ V/8 V};$
ADG408	±1	±100	±1	±100	nA max	Test Circuit 3
ADG409	±1	±50	±1	±50	nA max	
Channel ON Leakage ID, IS (ON)						$V_S = V_D = 8 \text{ V/0 V};$
ADG408	±1	$\pm 100$	±1	±100	nA max	Test Circuit 4
ADG409	±1	±50	±1	±50	nA max	
DIGITAL INPUTS						
Input High Voltage, V <sub>INH</sub>		2.4		2.4	V min	
Input Low Voltage, V <sub>INL</sub>		0.8		0.8	V max	
Input Current I <sub>INL</sub> or I <sub>INH</sub>		±10		±10	μA max	$V_{IN} = 0$ or $V_{DD}$
$C_{IN}$ , Digital Input Capacitance	8	±10	8	±10	pF typ	f = 1  MHz
DYNAMIC CHARACTERISTICS <sup>2</sup>					T JT	
	130		130		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ ;
t <sub>transition</sub>	150		150		по сур	$V_{S1} = 8 \text{ V/0 V}, V_{S8} = 0 \text{ V/8 V};$ Test Circuit 5
$t_{OPEN}$	10		10		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ ; $V_S = +5 V$ ; Test Circuit 6
$t_{ON}$ (EN)	140		140		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ ; $V_S = +5 V$ ; Test Circuit 7
$t_{OFF}$ (EN)	60		60		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ ; $V_S = +5 V$ ; Test Circuit 7
Charge Injection	5		5		pC typ	$V_S = 0$ V, $R_S = 0$ $\Omega$ , $C_L = 10$ nF; Test Circuit 8
OFF Isolation	-75		-75		dB typ	$R_L = 1 \text{ k}\Omega, f = 100 \text{ kHz};$ $V_{EN} = 0 \text{ V}; \text{ Test Circuit 9}$
Channel-to-Channel Crosstalk	85		85		dB typ	$R_L = 1 \text{ k}\Omega, \text{ f} = 100 \text{ kHz};$ Test Circuit 10
C <sub>S</sub> (OFF) C <sub>D</sub> (OFF)	11		11		pF typ	f = 1 MHz f = 1 MHz
ADG408	40		40		pF typ	1 – 1 WH12
ADG409	20		20		pF typ	
$C_D$ , $C_S$ (ON)			-		F -7F	f = 1 MHz
ADG408	54		54		pF typ	
ADG409	34		34		pF typ	
POWER REQUIREMENTS						
$ m I_{DD}$		1		1	μA typ	$V_{IN} = 0 \text{ V}, V_{EN} = 0 \text{ V}$
T	100	5	100	5	μA max	$\mathbf{X} = 0\mathbf{X}\mathbf{X} = 0\mathbf{A}\mathbf{X}$
$ m I_{DD}$	100 200	500	100 200	500	μA typ	$V_{IN} = 0 \text{ V}, V_{EN} = 2.4 \text{ V}$
	200	J00 	200	J00	μA max	

## NOTES

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 $<sup>^1</sup>Temperature \ ranges \ are \ as follows: B Version: -40 °C to +85 °C; T Version: -55 °C to +125 °C.$ 

<sup>&</sup>lt;sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

## ABSOLUTE MAXIMUM RATINGS1

$(T_{\lambda})$	= +25°C	unless	otherwise	noted)

· ·
$V_{DD}$ to $V_{SS}$ +44 V
$V_{DD}$ to GND0.3 V to +25 V
$V_{SS}$ to GND +0.3 V to -25 V
Analog, Digital Inputs <sup>2</sup> $V_{SS}$ –2 V to $V_{DD}$ +2 V or 20 mA,
Whichever Occurs First
Continuous Current, S or D
Peak Current, S or D
(Pulsed at 1 ms, 10% Duty Cycle max) 40 mA
Operating Temperature Range
Industrial (B Version)40°C to +85°C
Extended (T Version)55°C to +125°C
Storage Temperature Range65°C to +150°C
Junction Temperature +150°C
Cerdip Package, Power Dissipation 900 mW
$\theta_{JA}$ , Thermal Impedance
Lead Temperature, Soldering (10 sec) +300°C
Plastic Package, Power Dissipation
$\theta_{IA}$ , Thermal Impedance
Lead Temperature, Soldering (10 sec) +260°C
TSSOP Package, Power Dissipation
$\theta_{IA}$ , Thermal Impedance
$\theta_{\rm IC}$ , Thermal Impedance
SOIC Package, Power Dissipation
$\theta_{IA}$ , Thermal Impedance
Lead Temperature, Soldering
Vapor Phase (60 sec)+215°C
Infrared (15 sec) +220°C
NOTES

#### NOTES

## ORDERING INFORMATION

Model <sup>1</sup>	Temperature Range	Package Option <sup>2</sup>
ADG408BN	-40°C to +85°C	N-16
ADG408BR	-40°C to +85°C	R-16A
ADG408BRU	-40°C to +85°C	RU-16
ADG408TQ	-55°C to +125°C	Q-16
ADG409BN	-40°C to +85°C	N-16
ADG409BR	-40°C to +85°C	R-16A
ADG409TQ	-55°C to +125°C	Q-16

## NOTES

## CAUTION\_

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG408/ADG409 feature proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



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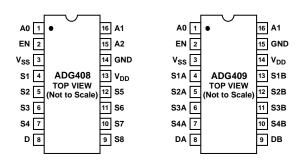
<sup>&</sup>lt;sup>1</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>&</sup>lt;sup>2</sup>Overvoltages at A, EN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

<sup>&</sup>lt;sup>1</sup>To order MIL-STD-883, Class B processed parts, add /883B to T grade part numbers.

 $<sup>^{2}</sup>$ N = Plastic DIP; Q = Cerdip; R = 0.15" Small Outline IC (SOIC); RU = Think Shrink Small Outline Package (TSSOP).

# PIN CONFIGURATIONS (DIP/SOIC/TSSOP)



## **ADG408 Truth Table**

A2	A1	A0	EN	ON SWITCH
X	X	X	0	NONE
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

## **ADG409 Truth Table**

Al	A0	EN	ON SWITCH PAIR
X	X	0	NONE
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

# **TERMINOLOGY**

$\overline{\mathrm{V}_{\mathrm{DD}}}$	Most positive power supply potential.
$V_{SS}$	Most negative power supply potential in dual supplies. In single supply applications, it may be connected to ground.
GND	Ground (0 V) reference.
$R_{ON}$	Ohmic resistance between D and S.
$\Delta R_{\rm ON}$	Difference between the R <sub>ON</sub> of any two channels.
I <sub>S</sub> (OFF)	Source leakage current when the switch is off.
$I_{D}$ (OFF)	Drain leakage current when the switch is off.
$I_D$ , $I_S$ (ON)	Channel leakage current when the switch is on.
$V_D(V_S)$	Analog voltage on terminals D, S.
C <sub>S</sub> (OFF)	Channel input capacitance for "OFF" condition.
C <sub>D</sub> (OFF)	Channel output capacitance for "OFF" condition.
$C_D$ , $C_S$ (ON)	"ON" switch capacitance.
$C_{IN}$	Digital input capacitance.
$t_{ON}$ (EN)	Delay time between the 50% and 90% points of the digital input and switch "ON" condition.
t <sub>OFF</sub> (EN)	Delay time between the 50% and 90% points of the digital input and switch "OFF" condition.
t <sub>TRANSITION</sub>	Delay time between the 50% and 90% points of the digital inputs and the switch "ON" condition when switching from one address state to another.
t <sub>OPEN</sub>	"OFF" time measured between the 80% point of both switches when switching from one address state to another.
$V_{INL}$	Maximum input voltage for Logic "0."
$V_{INH}$	Minimum input voltage for Logic "1."
$I_{INL}$ $(I_{INH})$	Input current of the digital input.
Crosstalk	A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an "OFF" channel.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
$I_{DD}$	Positive supply current.
$I_{SS}$	Negative supply current.

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# **Typical Performance Characteristics**

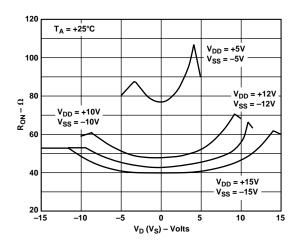
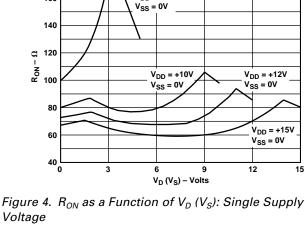


Figure 1.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Dual Supply Voltage



 $V_{DD} = +5V$ 

T<sub>A</sub> = +25°C

180

160

Voltage

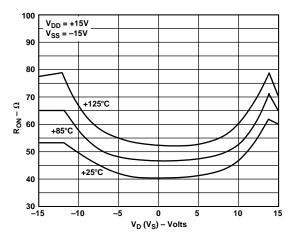


Figure 2.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different **Temperatures** 

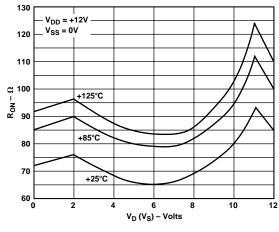


Figure 5.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different **Temperatures** 

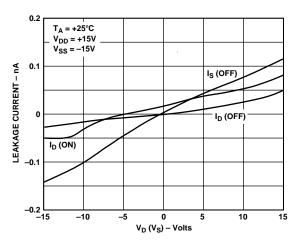


Figure 3. Leakage Currents as a Function of  $V_D$  ( $V_S$ )

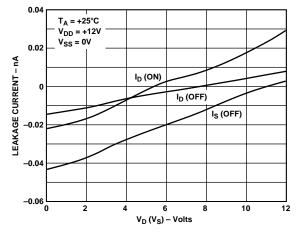


Figure 6. Leakage Currents as a Function of  $V_D$  ( $V_S$ )

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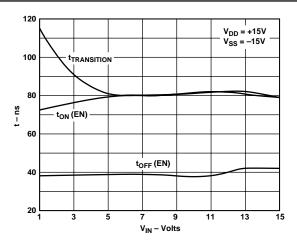


Figure 7. Switching Time vs. V<sub>IN</sub> (Bipolar Supply)

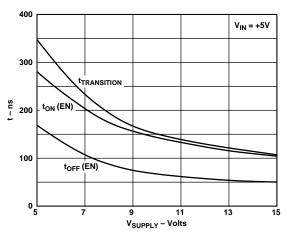


Figure 8. Switching Time vs. Single Supply

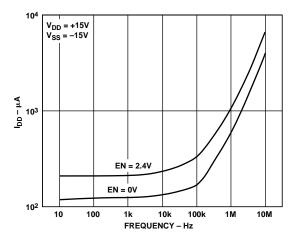


Figure 9. Positive Supply Current vs. Switching Frequency

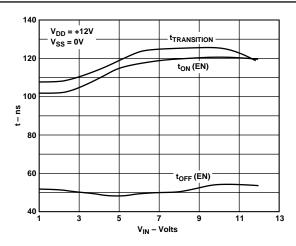


Figure 10. Switching Time vs. V<sub>IN</sub> (Single Supply)

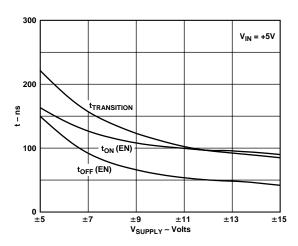


Figure 11. Switching Time vs. Bipolar Supply

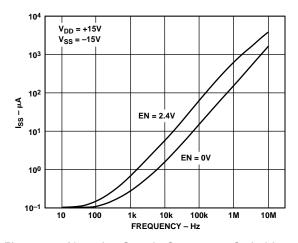


Figure 12. Negative Supply Current vs. Switching Frequency

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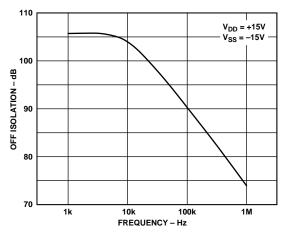


Figure 13. Off Isolation vs. Frequency

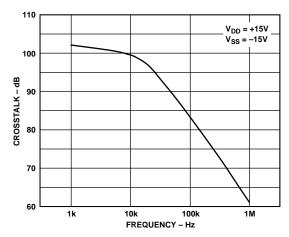
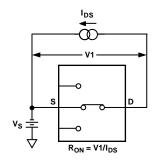
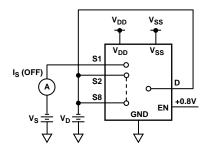


Figure 14. Crosstalk vs. Frequency

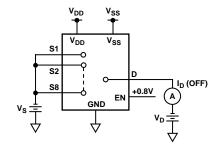
# **Test Circuits**



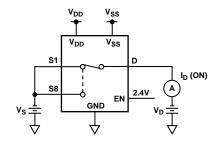
Test Circuit 1. On Resistance



Test Circuit 2. I<sub>S</sub> (OFF)

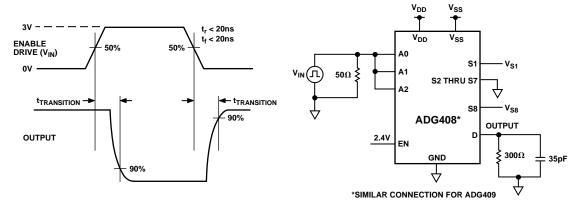


Test Circuit 3.  $I_D$  (OFF)

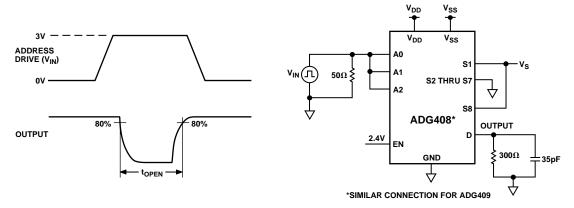


Test Circuit 4. I<sub>D</sub> (ON)

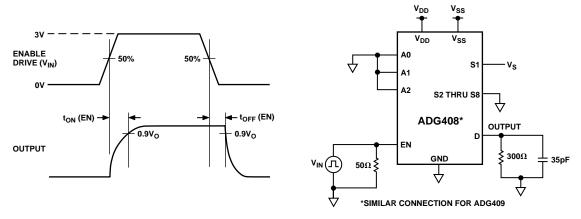
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Test Circuit 5. Switching Time of Multiplexer,  $t_{TRANSITION}$ 

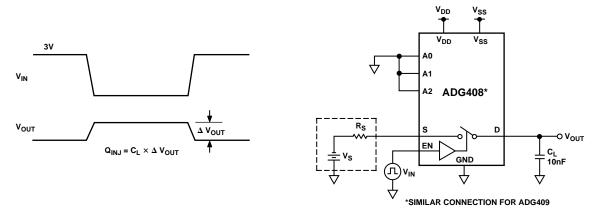


Test Circuit 6. Break-Before-Make Delay, t<sub>OPEN</sub>

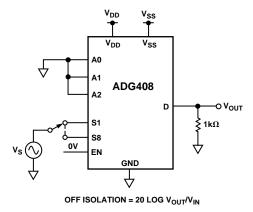


Test Circuit 7. Enable Delay,  $t_{ON}$  (EN),  $t_{OFF}$  (EN)

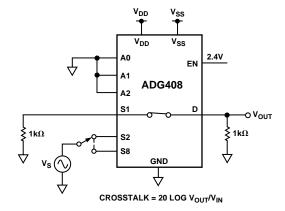
REV. A –9–



Test Circuit 8. Charge Injection



Test Circuit 9. OFF Isolation

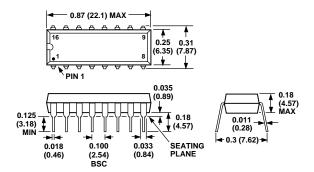


Test Circuit 10. Channel-to-Channel Crosstalk

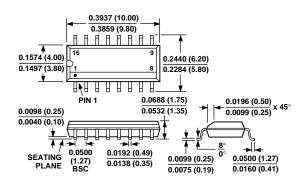
## **OUTLINE DIMENSIONS**

Dimensions shown in inches and (mm).

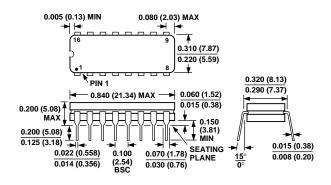
## Plastic DIP (N-16)



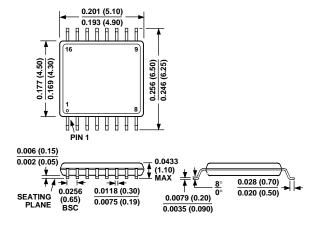
## SO (Narrow Body) (R-16A)



## Cerdip (Q-16)



# Thin Shrink Small Outline Package (TSSOP) (RU-16)



REV. A –11–